

1N5419
1N5420

**FAST RECOVERY GLASS
PASSIVATED SILICON RECTIFIER
3 AMP, 500 AND 600 VOLTS**



GPR-4AM CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 1N5419 and 1N5420 are Silicon Rectifiers mounted in a hermetically sealed, glass passivated package, designed for general purpose applications where fast reverse recovery times and high reliability are required.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	1N5419	1N5420	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	500	600	V
DC Blocking Voltage	V_R	500	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	350	420	V
Average Forward Current ($T_A=55^\circ\text{C}$)	I_O	3.0		A
Peak Forward Surge Current, $t_p=8.3\text{ms}$	I_{FSM}	80		A
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

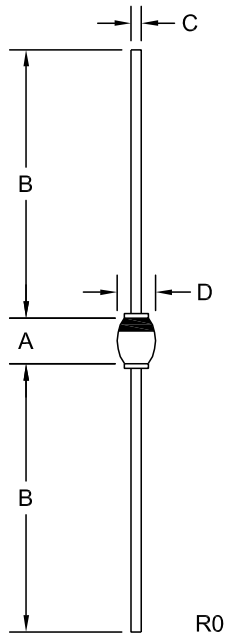
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$		1.0	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=100^\circ\text{C}$		20	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=175^\circ\text{C}$		2.0	mA
V_F	$I_F=3.0\text{A}$		1.1	V
V_F	$I_F=9.0\text{A}$		1.5	V
BV_R	$I_R=50\mu\text{A}$ (1N5419)	550		V
BV_R	$I_R=50\mu\text{A}$ (1N5420)	660		V
C_J	$V_R=12\text{V}, f=1.0\text{MHz}$ (1N5419)		110	pF
C_J	$V_R=12\text{V}, f=1.0\text{MHz}$ (1N5420)		100	pF
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$ (1N5419)		250	ns
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$ (1N5420)		400	ns

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GPR-4AM CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.165	0.189	4.20	4.80
B	1.024	---	26.00	---
C	0.037	0.042	0.95	1.06
D	0.130	0.175	3.30	4.45

GPR-4AM (REV: R0)

R2 (11-April 2011)